

AMENDMENTS TO THE DRAWINGS

Replacement sheets are attached. Fig. 1(a), 1(b), 2(a), 2(b) and 2(c) are now labeled as "prior art."

REMARKS

By this Amendment, claim 11 is cancelled and claims 12 and 15 are amended. Accordingly, claims 1-10 and 12-15 are pending in the current application.

The objection to claims 3-10, 14 and 15 is noted. However, it is respectfully pointed out to the Examiner that Applicants filed a Preliminary Amendment on April 7, 2006, to address these claim objections. To date, it appears that the Preliminary Amendment has not been considered by the Examiner. Applicants filed a Communication on December 23, 2008, specifically requesting that the Preliminary Amendment be considered. Accordingly, Applicants respectfully submit that these claim objections are moot.

Claims 1-10 stand rejected under 35 U.S.C. § 112, ¶ 2 as being indefinite. The Office Action contends that it is unclear how “the buried conductor interconnect connects one of the source and drain regions of the semiconductor raised portion and another conductive portion below the interlayer insulating film.” Applicants respectfully disagree.

As shown, for example, in Fig. 4(a) and Fig. 4(c), the buried conductor interconnect (411) extending along line B-B connects the source/drain region (406) in the raised portion (403) of the left transistor to the source/drain region (406) in the raised portion (403) of the right transistor. It is the source/drain region in the raised portion of the right transistor that corresponds to, for example, the “another conductive portion” recited in claim 1.

Additionally, in Fig. 11(a) and Fig. 11(b), the buried conductor interconnect (411c) extending along line A-A connects the source/drain region (406) in the raised portion (403a) of the left transistor to the gate electrode (404b) of the right transistor (which has the raised portion (403b)). The gate electrode (404b) of the right transistor also corresponds to the “another conductive portion” recited in claim 1. Applicants respectfully submit that Figs. 4(a), 4(c), 11(a), and 11(b) make clear the language of claims 1-10, and respectfully request this rejection be withdrawn.

Claims 1, 3, 7, and 8 stand rejected under 35 U.S.C. § 102(e) as anticipated by Yeo et al. (U.S. Patent No. 6,867,433) (hereinafter “Yeo I”). Claim 2 stands rejected under 35 U.S.C. § 103(a) as being unpatentable over Yeo I in view of Yeo (U.S. Patent No. 7,105,894) (hereinafter “Yeo II”). Claims 4-6 and 9-15 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Yeo I in view of Wang et al. (U.S. Patent Publication 2005/0029556). Applicants respectfully traverse these rejections.

Among the limitations of independent claims 1 and 12 which are neither disclosed nor suggested in the prior art of record is a semiconductor device where “the buried conductor interconnect connects one of the source and drain regions of the semiconductor raised portion and another conductive portion below the interlayer insulating film.”

The Office Action equates conductive material 196 in Yeo I to the “buried conductive interconnect/another conductive portion” recited in claim 1 of the present application. However, conductive material 196 cannot correspond to the claimed “another conductive portion” because conductive material 196 of Yeo I is not “below the interlayer insulating film.”

In Fig. 12j of Yeo I, conductive material 196 connects source region 172 (or drain region 174) to metallization layer 198. Metallization layer 198 is formed above passivation layer 194. Thus, metallization layer 198 that is connected to conductive material 196 is not formed below passivation layer 194. Accordingly, Yeo I does not teach or suggest the present invention as defined in independent claims 1 and 12.

Neither Yeo II nor Wang et al. remedy any of the deficiencies of Yeo I. None of these references teach or suggest a semiconductor device where “the buried conductor interconnect connects one of the source and drain regions of the semiconductor raised portion and another conductive portion below the interlayer insulating film” as required by independent claims 1 and 12. As such, even if one were to combine the teachings of Yeo I, Yeo II and/or Wang et al., one would not arrive at the present invention as defined in independent claims 1 and 12.

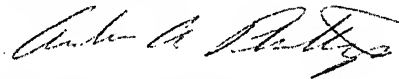
Accordingly, it is respectfully submitted that independent claims 1 and 12 patentably distinguish over the art of record.

Claims 2-10 depend either directly or indirectly from independent claim 1 and include all of the limitations found therein. Claims 13-15 each depend directly from independent claim 12 and include all of the limitations found therein. Each of these dependent claims include additional limitations which, in combination with the limitations of the claims from which they depend, are neither disclosed nor suggested in the art of record. Accordingly, claims 2-10 and 13-15 are likewise patentable.

In view of the foregoing, favorable consideration of the amendments to claims 12 and 15, and allowance of the present application with claims 1-10 and 12-15 is respectfully and earnestly solicited.

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Respectfully submitted,



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